



N-Channel Enhancement Mode Power MOSFET

The MX8806B uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V.

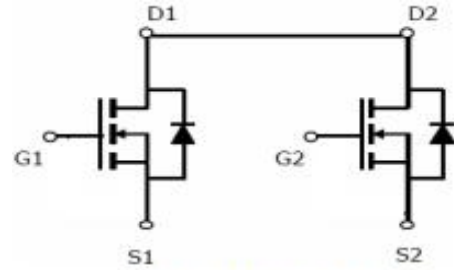
This device is suitable for use as a load switch or in PWM applications.

General Features

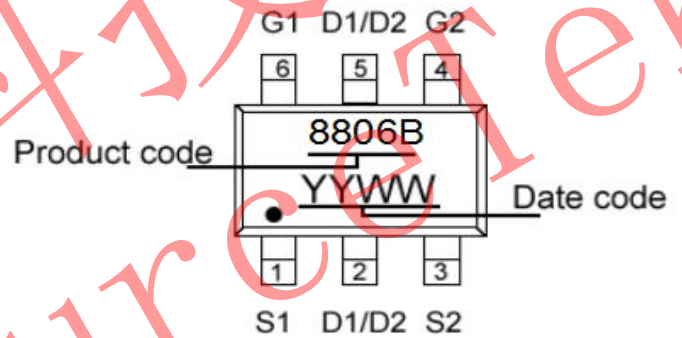
- ◆ $V_{DS} = 15V, I_D = 6A$
- ◆ $R_{DS(ON)} < 15m\Omega @ V_{GS} = 4.5V$
- ◆ $R_{DS(ON)} < 17m\Omega @ V_{GS} = 3.8V$
- ◆ $R_{DS(ON)} < 22m\Omega @ V_{GS} = 2.5V$
- ◆ High Power and current handing capability
- ◆ Lead free product is acquired
- ◆ Surface Mount Package

Applicatio

- ◆ PWM application
- ◆ Load switch



Schematic diagram



Marking and pin assignment
SOT-23-6 (TOP VIEW)

ASO Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	15	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	5	A
Drain Current-Pulsed (Note 1)	I_{DM}	20	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C



Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83.3	$^{\circ}C/W$
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Electrical Characteristics (TA=25 $^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	15	19	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=15V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	0.95	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=4.5A$	10	12.8	15	m Ω
		$V_{GS}=3.8V, I_D=4.0A$	11	13.5	17	m Ω
		$V_{GS}=2.5V, I_D=3.5A$	15.5	18.6	22	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$	-	20	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	1150	-	PF
Output Capacitance	C_{oss}		-	185	-	PF
Reverse Transfer Capacitance	C_{rss}		-	145	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=1.35\Omega$ $V_{GS}=5V, R_{GEN}=3\Omega$	-	6		nS
Turn-on Rise Time	t_r		-	13		nS
Turn-Off Delay Time	$t_{d(off)}$		-	52		nS
Turn-Off Fall Time	t_f		-	16		nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=5A,$ $V_{GS}=4.5V$	-	15		nC
Gate-Source Charge	Q_{gs}		-	0.8	-	nC
Gate-Drain Charge	Q_{gd}		-	3.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=1A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	7	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- Guaranteed by design, not subject to production



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

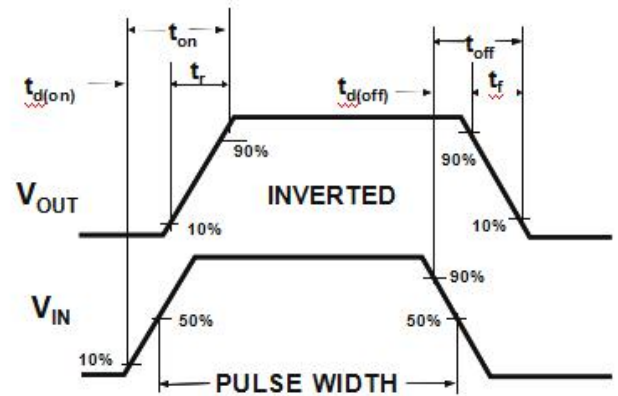
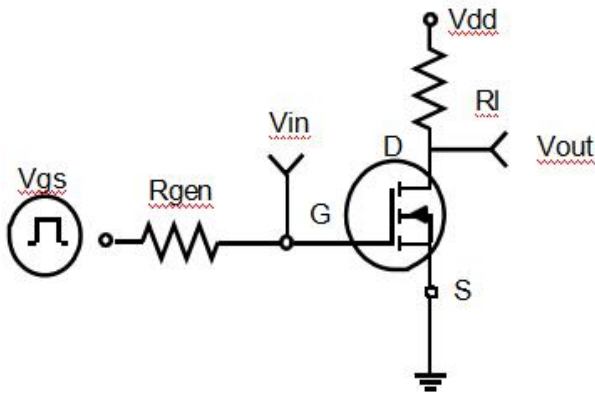


Figure 1: Switching Test Circuit

Figure 2: Switching Waveforms

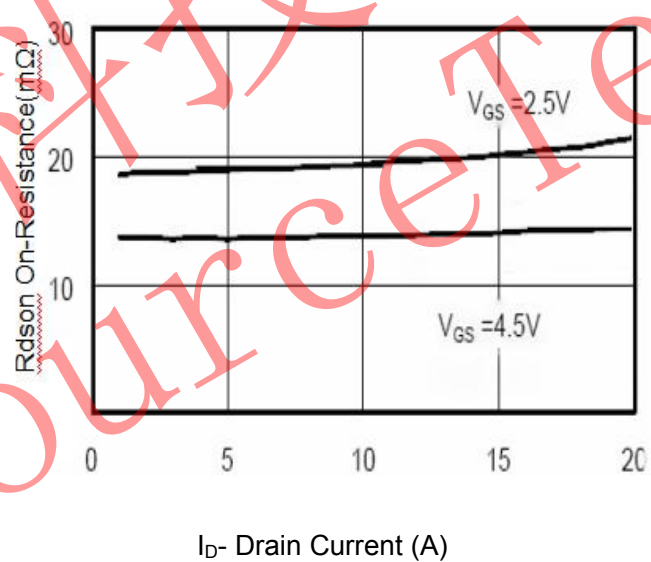
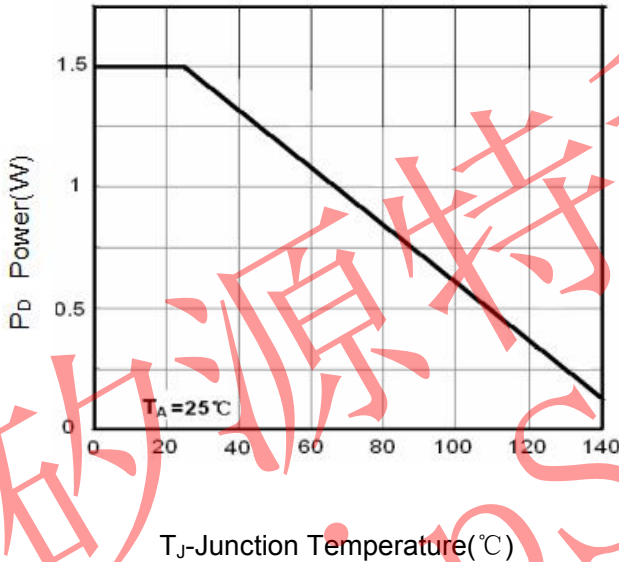
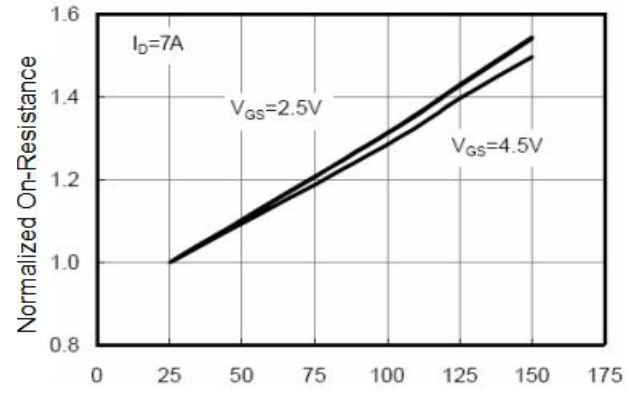
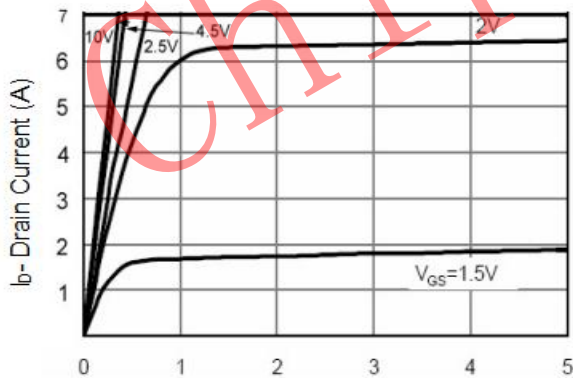


Figure 3 Power Dissipation

Figure 4 Drain-Source On-Resistance

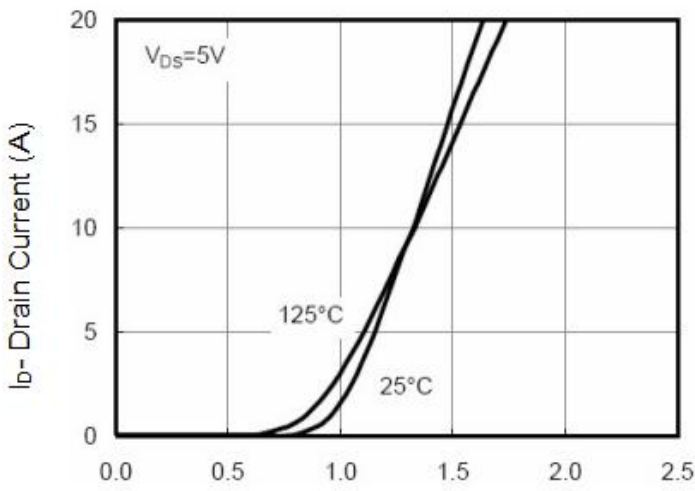


Vds Drain-Source Voltage (V)

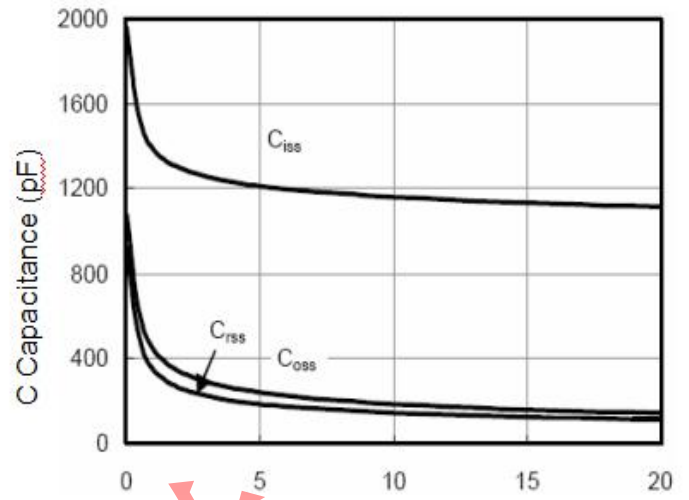
T_J-Junction Temperature(°C)

Figure 5 Output CHARACTERISTICS

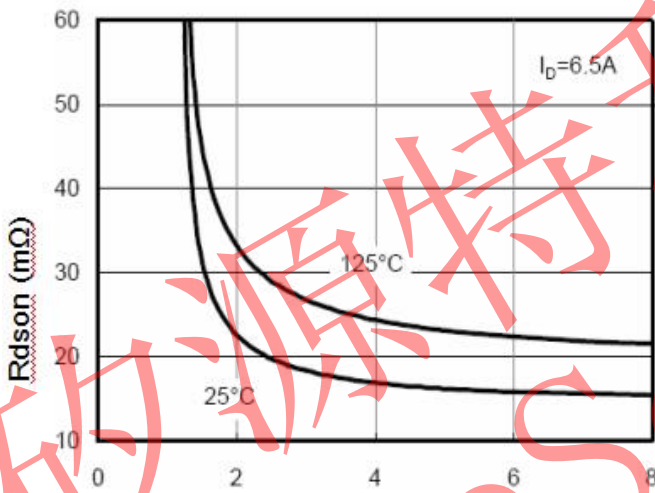
Figure 6 Drain-Source On-Resistance



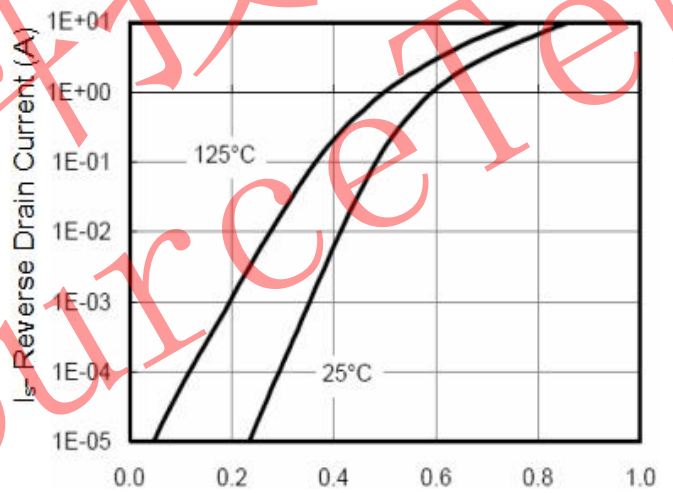
Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



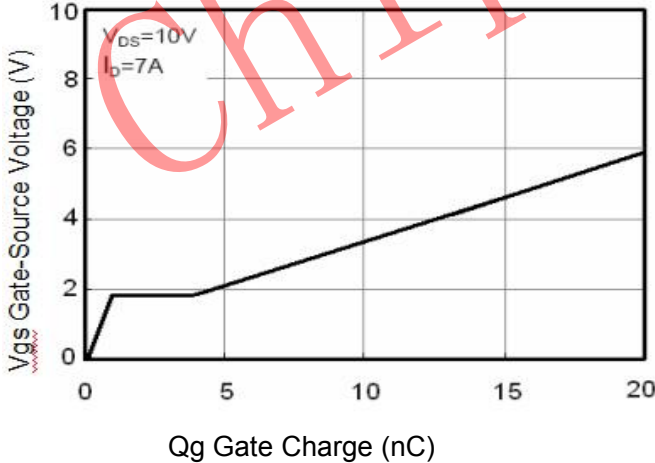
Vds Drain-Source Voltage (V)
Figure 8 Capacitance vs Vds



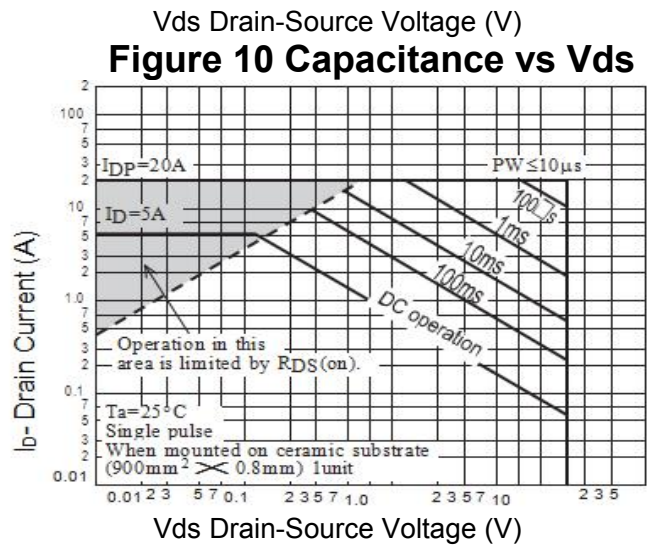
Vgs Gate-Source Voltage (V)
Figure 9 Rds(on) vs Vgs



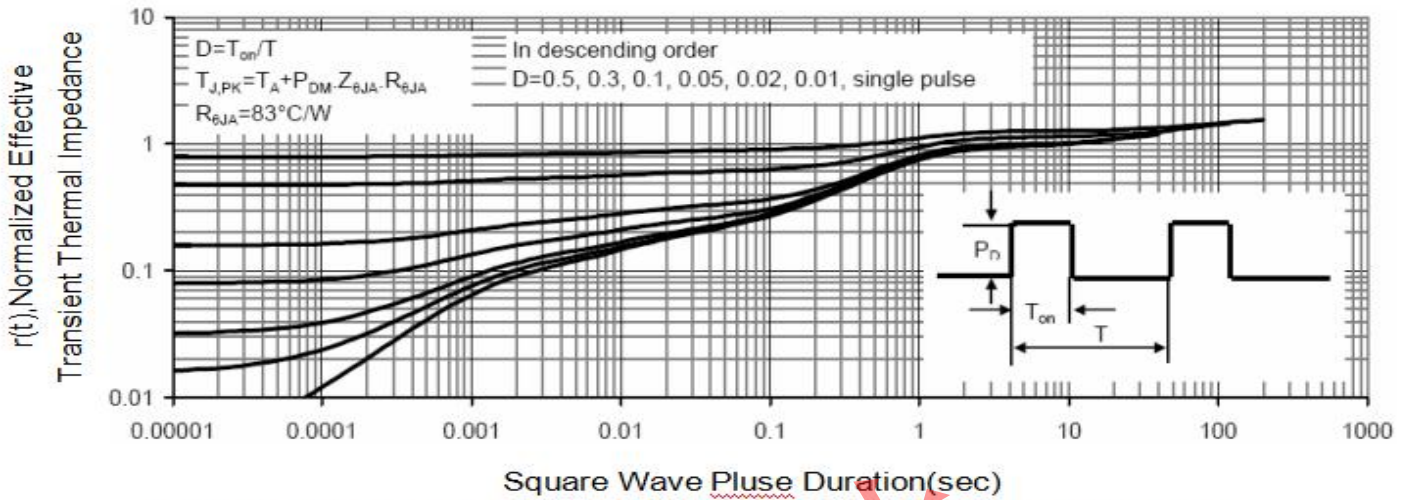
Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Qg Gate Charge (nC)
Figure 11 Gate Charge



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area



SOT23-6 PACKAGE INFOR

